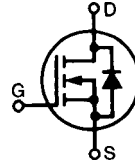


High Voltage MOSFET

IXTA 2N100 IXTP 2N100

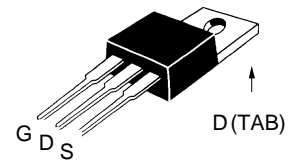
$V_{DSS} = 1000\text{ V}$
 $I_{D25} = 2\text{ A}$
 $R_{DS(on)} = 7\ \Omega$

N-Channel Enhancement Mode

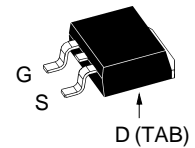


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	2	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	8	A
P_D	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		4	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-220AB (IXTP)



TO-263 AA (IXTA)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
 - easy to drive and to protect
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Flyback inverters
- DC choppers

Advantages

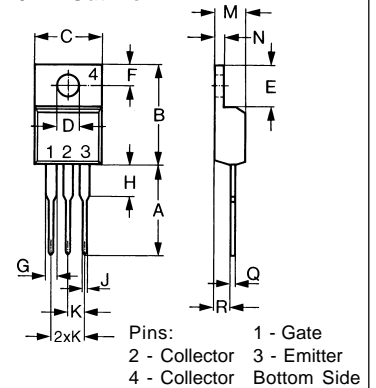
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 250\ \mu\text{A}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2		4.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$			200 μA
	$V_{GS} = 0\text{ V}$			1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5\ I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			7.0 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	1.5	2.2	S	
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		825	pF	
C_{oss}			58	pF	
C_{rss}			15	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 20\ \Omega$, (External)		15	30	ns
t_r			15	35	ns
$t_{d(off)}$			60	80	ns
t_f			30	55	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$			40	nC
Q_{gs}				10	nC
Q_{gd}				15	nC
R_{thJC}				1.25	K/W
R_{thCK}		0.25			K/W

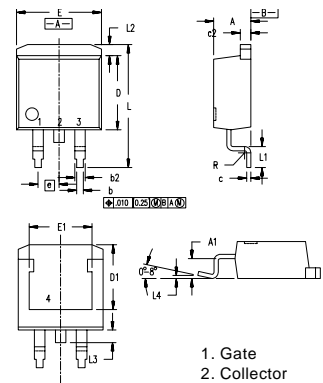
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
I_S	$V_{GS} = 0\text{ V}$			2	A
I_{SM}	Repetitive; pulse width limited by T_{JM}			8	A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5	V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	1000			ns

TO-220 AB Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

TO-263 SMD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

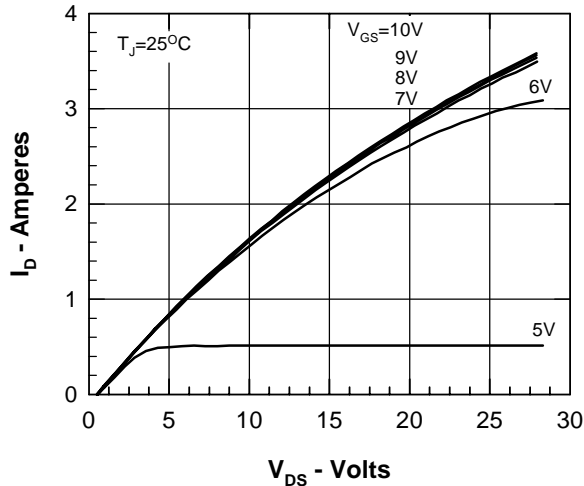


Figure 1. Output Characteristics at 25°C

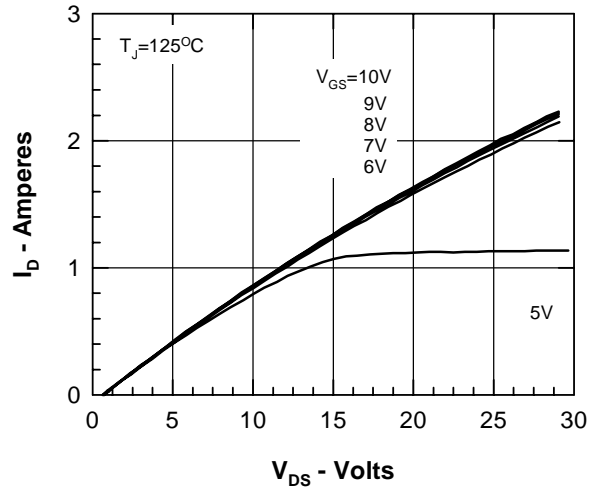


Figure 2. Output Characteristics at 125°C

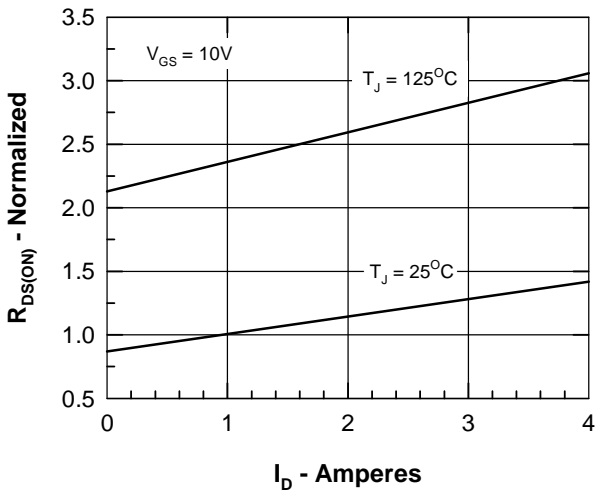


Figure 3. $R_{DS(on)}$ normalized to $0.5 I_{D25}$ value

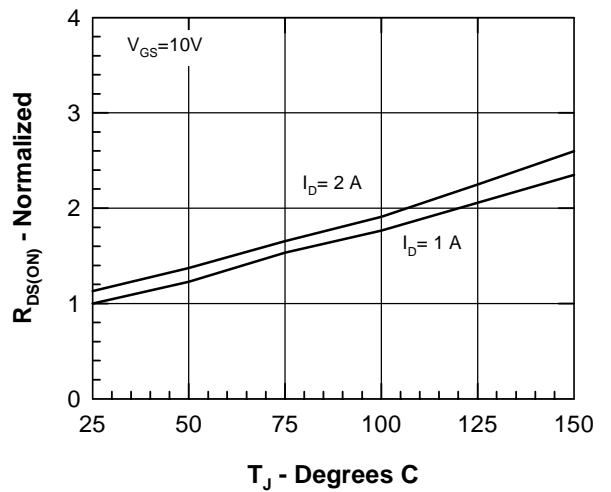


Figure 4. $R_{DS(on)}$ normalized to $0.5 I_{D25}$ value

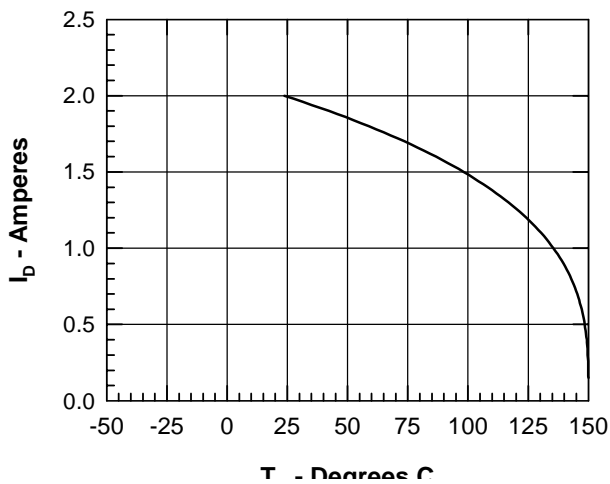


Figure 5. Drain Current vs. Case Temperature

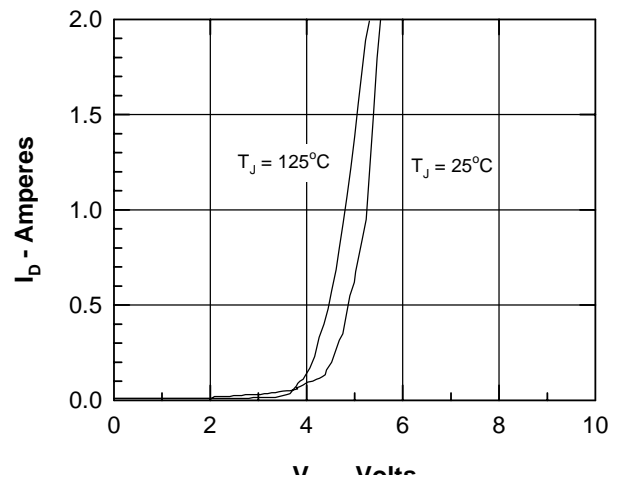


Figure 6. Admittance Curves

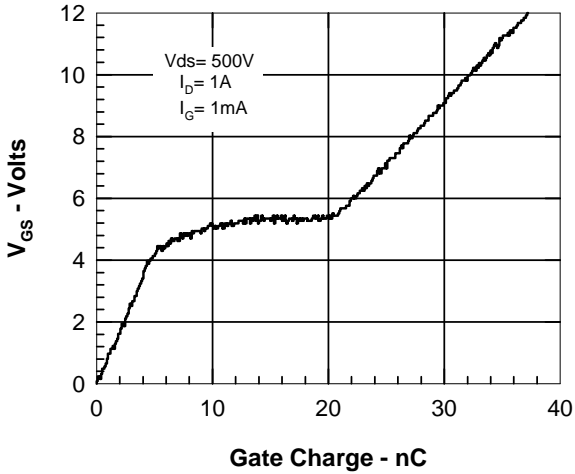


Figure 7. Gate Charge

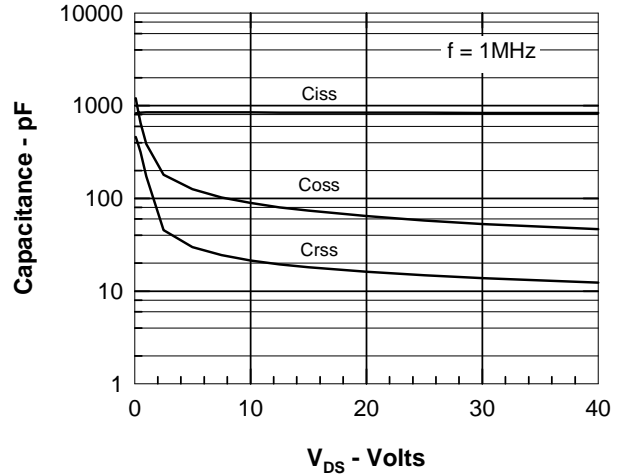


Figure 8. Capacitance Curves

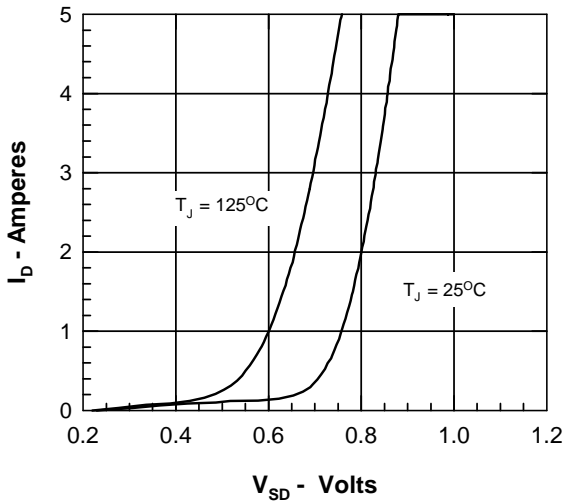


Figure 9. Source Current vs. Source to Drain Voltage

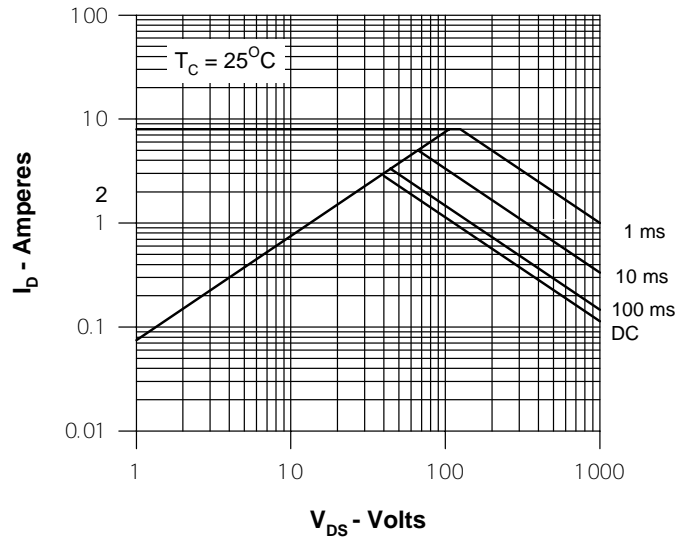


Figure 10. Forward Bias Safe Operating Area

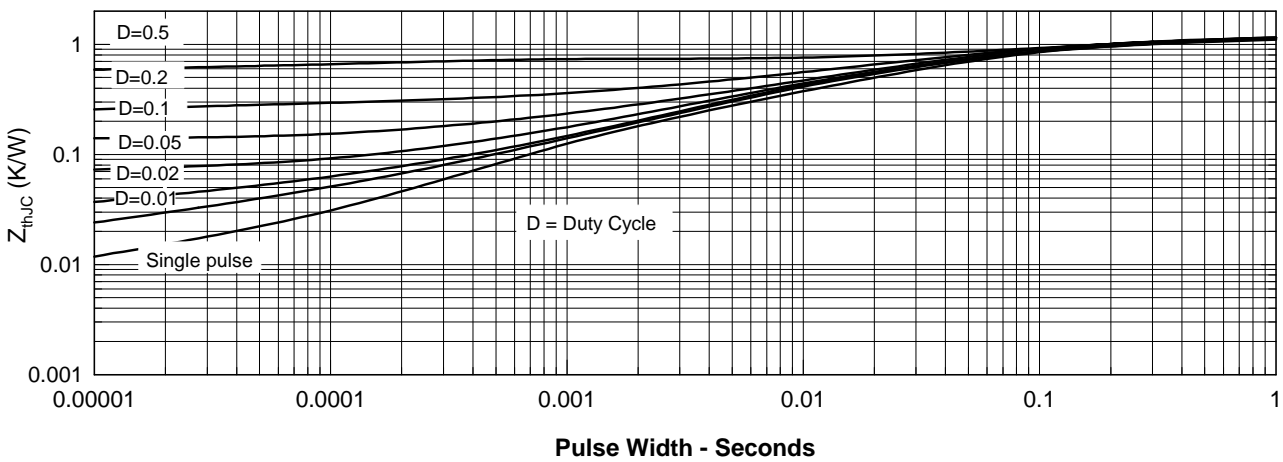


Figure 11. Transient Thermal Resistance